

Please substitute the following amended claim(s) for corresponding claim(s) previously presented. A copy of the amended claim(s) showing current revisions is attached.

1. (*Unamended*) A semiconductor laser device comprising:  
a plurality of semiconductor laser resonators having light emitting layers of materials different from each other, the semiconductor laser resonators being provided on the same semiconductor substrate so that the light emitting layers lie substantially in parallel to a main surface of the semiconductor substrate, and  
a high-resistance region provided between the semiconductor laser resonators.

Q1  
4. (*Amended*) The semiconductor laser device according to claim 1, wherein the semiconductor laser resonators comprise two resonators having oscillation wavelengths in a red region and an infrared region, respectively.

Q2 Sub (27)  
10. (*Amended*) The semiconductor laser device according to claim 9, wherein the high - resistivity semiconductor layer is formed by implanting protons or gallium ions.

Please add the following new claims:

Q3 Sub (37)  
16. (*New*) A semiconductor laser device comprising: